

# JFET Input Operational Amplifiers

These low cost JFET input operational amplifiers combine two state—of—the—art analog technologies on a single monolithic integrated circuit. Each internally compensated operational amplifier has well matched high voltage JFET input devices for low input offset voltage. The BIFET technology provides wide bandwidths and fast slew rates with low input bias currents, input offset currents, and supply currents.

The ON Semiconductor BIFET family offers single, dual and quad operational amplifiers which are pin–compatible with the industry standard MC1741, MC1458, and the MC3403/LM324 bipolar devices. The MC34001/34002/34004 series are specified from 0° to +70°C.

Input Offset Voltage Options of 5.0 mV and 10 mV Maximum

Low Input Bias Current: 40 pA
Low Input Offset Current: 10 pA
Wide Gain Bandwidth: 4.0 MHz

• High Slew Rate: 13 V/μs

• Low Supply Current: 1.4 mA per Amplifier

• High Input Impedance:  $10^{12} \Omega$ 

• High Common Mode and Supply Voltage Rejection Ratios: 100 dB

Industry Standard Pinouts

### MC34001, B MC34002, B MC34004, B

## JFET INPUT OPERATIONAL AMPLIFIERS

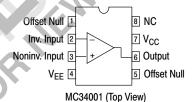


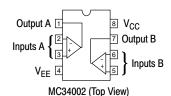




D SUFFIX
PLASTIC PACKAGE
CASE 751
(SO-8)

### **PIN CONNECTIONS**

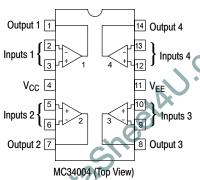






P SUFFIX PLASTIC PACKAGE CASE 646

### **PIN CONNECTIONS**



### ORDERING INFORMATION

Op Amp Function	Device	Operating Temperature Range	Package
Cinala	MC34001BD, D	T 00 to 1 700C	SO-8
Single	MC34001BP, P	$T_A = 0^{\circ} \text{ to+ } 70^{\circ}\text{C}$	Plastic DIP
	MC34002BD, D	T 00 to 1700C	SO-8
Dual	MC34002BP, P	$T_A = 0^{\circ} \text{ to } +70^{\circ}\text{C}$	Plastic DIP
Quad	MC34004BP, P	$T_A = 0^{\circ} \text{ to } +70^{\circ}\text{C}$	Plastic DIP

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Supply Voltage	$V_{CC}, V_{EE}$	±18	V
Differential Input Voltage (Note 1)	V <sub>ID</sub>	±30	V
Input Voltage Range	V <sub>IDR</sub>	±16	V
Open Short Circuit Duration	t <sub>SC</sub>	Continuous	
Operating Ambient Temperature Range	T <sub>A</sub>	0 to +70	°C
Operating Junction Temperature	TJ	150	°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

**NOTES:** 1. Unless otherwise specified, the absolute maximum negative input voltage is equal to the negative power supply.

### **ELECTRICAL CHARACTERISTICS** ( $V_{CC}$ = +15 V, $V_{EE}$ = -15 V, $T_A$ = 25°C, unless otherwise noted.)

Characteristics	Symbol	Min	Тур	Max	Unit
Input Offset Voltage (R <sub>S</sub> ≤ 10 k) MC3400XB MC3400X	V <sub>IO</sub>	_	3.0 5.0	5.0 10	mV
Average Temperature Coefficient of Input Offset Voltage $R_S \le 10 \text{ k}$ , $T_A = T_{low}$ to $T_{high}$ (Note 2)	$\Delta V_{IO}/\Delta T$		10	_	μV/°C
Input Offset Current (V <sub>CM</sub> = 0) (Note 3) MC3400XB MC3400X	I <sub>IO</sub>	7	25 25	100 100	рА
Input Bias Current (V <sub>CM</sub> = 0) (Note 3) MC3400XB MC3400X	I <sub>IB</sub>	_	50 50	200 200	рА
Input Resistance	ri	_	10 <sup>12</sup>	_	Ω
Common Mode Input Voltage Range	V <sub>ICR</sub>	±11 —	+15 -12	_	V
Large Signal Voltage Gain ( $V_O = \pm 10 \text{ V}$ , $R_L = 2.0 \text{ k}$ ) MC3400XB MC3400X	A <sub>VOL</sub>	50 25	150 100		V/mV
Output Voltage Swing $ (R_L \geq 10 \text{ k}) \\ (R_L \geq 2.0 \text{ k}) $	Vo	±12 ±10	±14 ±13		V
Common Mode Rejection Ratio (R <sub>S</sub> ≤ 10 k) MC3400XB MC3400X	CMRR	80 70	100 100		dB
Supply Voltage Rejection Ratio (R <sub>S</sub> ≤ 10 k) (Note 4) MC3400XB MC3400X	PSRR	80 70	100 100	_	dB
Supply Current (Each Amplifier) MC3400XB MC3400X	I <sub>D</sub>	_	1.4 1.4	2.5 2.7	mA
Slew Rate ( $A_V = 1.0$ )	SR	_	13	_	V/μs
Gain-Bandwidth Product	GBW	_	4.0	_	MHz
Equivalent Input Noise Voltage $(R_S = 100 \Omega, f = 1000 Hz)$	e <sub>n</sub>	_	25	_	nV/√Hz
Equivalent Input Noise Current (f = 1000 Hz)	i <sub>n</sub>	_	0.01	_	pA/√Hz

**NOTES:** 2. T<sub>low</sub> = 0°C for MC34001/34001B MC34002 MC34004/34004B T<sub>high</sub> = +70°C for MC34001/34001B MC34002 MC34004/34004B

3. The input bias currents approximately double for every 10°C rise in junction temperature, T<sub>J</sub>. Due to limited test time, the input bias currents are correlated to junction temperature. Use of a heatsink is recommended if input bias current is to be kept to a minimum.

correlated to junction temperature. Use of a heatsink is recommended if input bias current is to be kept to a minimum.

4. Supply voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously, in accordance with common practice.

### **ELECTRICAL CHARACTERISTICS** ( $V_{CC} = +15 \text{ V}$ , $V_{EE} = -15 \text{ V}$ , $T_A = T_{low}$ to $T_{high}$ [Note 2].)

$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{l} \text{MC3400XB} \\ \text{MC3400X} \\ \\ \text{Input Offset Current ($V_{CM} = 0$) (Note 3$)} \\ \text{MC3400XB} \\ \text{MC3400X} \\ \\ \text{Input Bias Current ($V_{CM} = 0$) (Note 3$)} \\ \text{MC3400XB} \\ \text{MC3400X} \\ \\ \text{Common Mode Input Voltage Range} \\ \\ \text{Large Signal ($V_{O} = \pm 10 \text{ V}, R_{L} = 2.0 \text{ k}$)} \\ \text{MC3400XB} \\ \text{MC3400XB} \\ \text{MC3400X} \\ \\ \text{Output Voltage Swing} \\ (R \geq 10 \text{ k}$) \\ \end{array}$	I <sub>IO</sub>			4.0 4.0	1
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Input Offset Current ( $V_{CM} = 0$ ) (Note 3) MC3400XB MC3400X  Input Bias Current ( $V_{CM} = 0$ ) (Note 3) MC3400XB MC3400X  Common Mode Input Voltage Range  Large Signal ( $V_{O} = \pm 10 \text{ V}$ , $R_{L} = 2.0 \text{ k}$ ) MC3400XB MC3400X  Output Voltage Swing ( $R \ge 10 \text{ k}$ )	I <sub>IB</sub>			4.0 4.0	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\label{eq:mc3400xB} \begin{split} &\text{MC3400X} \\ &\text{Input Bias Current (V}_{\text{CM}} = 0) \text{ (Note 3)} \\ &\text{MC3400XB} \\ &\text{MC3400X} \\ &\text{Common Mode Input Voltage Range} \\ &\text{Large Signal (V}_{\text{O}} = \pm 10 \text{ V, R}_{\text{L}} = 2.0 \text{ k)} \\ &\text{MC3400XB} \\ &\text{MC3400X} \\ &\text{Output Voltage Swing} \\ &\text{(R} \geq 10 \text{ k)} \end{split}$	I <sub>IB</sub>	     ±11	_ 	4.0	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\label{eq:mc3400xB} \begin{split} &\text{MC3400X} \\ &\text{Common Mode Input Voltage Range} \\ &\text{Large Signal (V}_{\text{O}} = \pm 10 \text{ V}, \text{ R}_{\text{L}} = 2.0 \text{ k}) \\ &\text{MC3400XB} \\ &\text{MC3400X} \\ &\text{Output Voltage Swing} \\ &\text{(R} \geq 10 \text{ k}) \end{split}$	V <sub>ICR</sub>	_ _ _ ±11		8.0	
	Large Signal ( $V_O = \pm 10 \text{ V}$ , $R_L = 2.0 \text{ k}$ ) MC3400XB MC3400X  Output Voltage Swing ( $R \ge 10 \text{ k}$ )		±11			
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	MC3400XB MC3400X  Output Voltage Swing (R ≥ 10 k)	A <sub>VOL</sub>		_	_	
$(R \geq 10 \text{ k}) \\ (R \geq 2.0 \text{ k}) \\ \\ \hline \\ Common Mode Rejection Ratio (R_S \leq 10 \text{ k}) \\ MC3400XB \\ MC3400X \\ \hline \\ MC3400X \\ \hline \\ MC3400X \\ \hline \\ MC3400XB \\ MC3400X \\ \hline \\ MC3400XB \\ \hline \\ MC3400X \\ \hline \\ MC340X \\ \hline \\ MC3$	(R ≥ 10 k)			_		ν
MC3400XB MC3400X  Supply Voltage Rejection Ratio (R <sub>S</sub> ≤ 10 k) (Note 4) MC3400XB MC3400X  Supply Current (Each Amplifier) MC3400X  Supply Current (Each Amplifier) MC3400XB MC3400X  MC3400X  NOTES: 2. T <sub>Iow</sub> = 0°C for MC34001/34001B MC34002 MC34004/34004B  3. The input bias currents approximately double for every 10°C rise in junction temperature, T <sub>J</sub> . Due to limited test time, the input bias currents are correlated to junction temperature. Use of a heatsink is recommended if input bias current is to be kept to a minimum.  4. Supply voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously, in accordance with common p	(11 = 2.0 K)	Vo		_		
MC3400XB MC3400X  Supply Current (Each Amplifier) MC3400XB MC3400X  NOTES: 2. T <sub>low</sub> = 0°C for MC34001/34001B MC34002 MC34004/34004B  3. The input bias currents approximately double for every 10°C rise in junction temperature, T <sub>J</sub> . Due to limited test time, the input bias currents are correlated to junction temperature. Use of a heatsink is recommended if input bias current is to be kept to a minimum.  4. Supply voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously, in accordance with common p	MC3400XB	CMRR		14	=	
MC3400XB MC3400X  NOTES: 2. T <sub>low</sub> = 0°C for MC34001/34001B MC34002 MC34004/34004B  3. The input bias currents approximately double for every 10°C rise in junction temperature, T <sub>J</sub> . Due to limited test time, the input bias currents are correlated to junction temperature. Use of a heatsink is recommended if input bias current is to be kept to a minimum.  4. Supply voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously, in accordance with common p	MC3400XB	PSRR				
MC34002 MC34004/34004B  3. The input bias currents approximately double for every 10°C rise in junction temperature, T <sub>J</sub> . Due to limited test time, the input bias currents at correlated to junction temperature. Use of a heatsink is recommended if input bias current is to be kept to a minimum.  4. Supply voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously, in accordance with common p	MC3400XB	ID	_	_ _		
	4. Supply voltage rejection ratio is measured for both supply magnitudes increasing	ing or decreasing	g simultaneous	lly, in accordan	ice with comm	on pr

<sup>3.</sup> The input bias currents approximately double for every 10°C rise in junction temperature, T<sub>J</sub>. Due to limited test time, the input bias currents are correlated to junction temperature. Use of a heatsink is recommended if input bias current is to be kept to a minimum.

<sup>4.</sup> Supply voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously, in accordance with common practice.

Figure 1. Input Bias Current versus Temperature

Figure 2. Output Voltage Swing versus Frequency

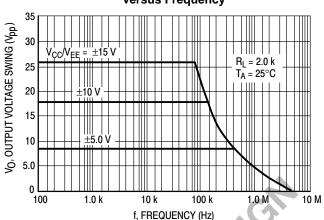


Figure 3. Output Voltage Swing versus Load Resistance

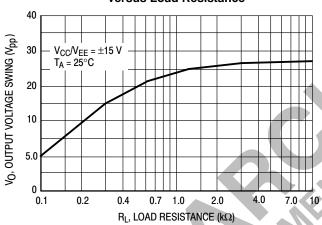


Figure 4. Output Voltage Swing versus Supply Voltage

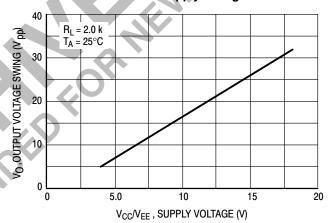


Figure 5. Output Voltage Swing versus Temperature

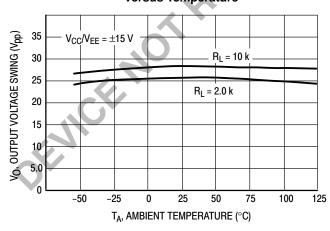


Figure 6. Supply Current per Amplifier versus Temperature

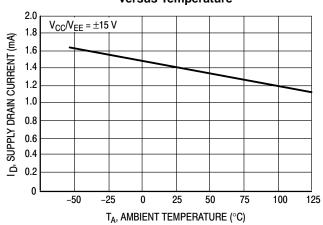


Figure 7. Large–Signal Voltage Gain and Phase Shift versus Frequency

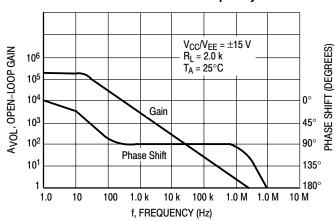


Figure 8. Large-Signal Voltage Gain versus Temperature

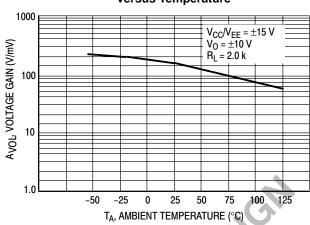


Figure 9. Normalized Slew Rate versus Temperature

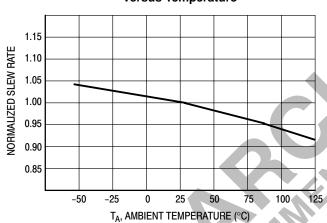


Figure 10. Equivalent Input Noise Voltage

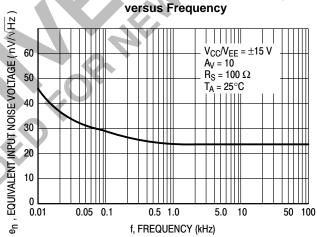
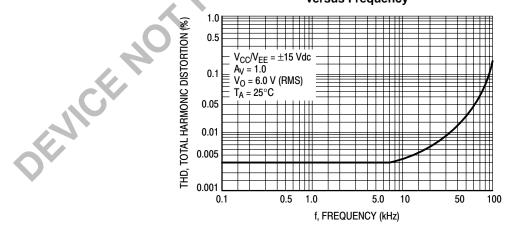


Figure 11. Total Harmonic Distortion versus Frequency



### Representative Circuit Schematic (Each Amplifier)

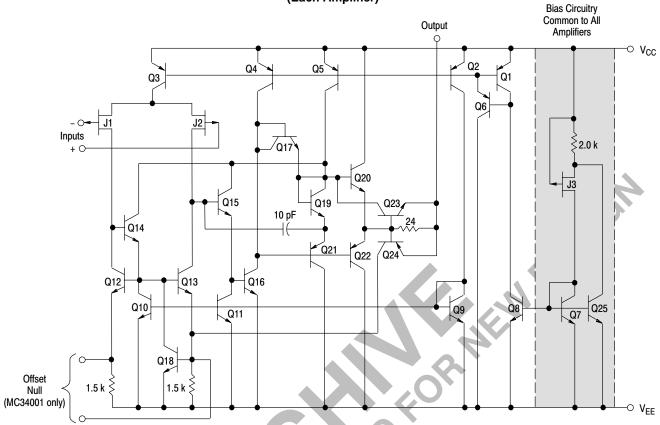
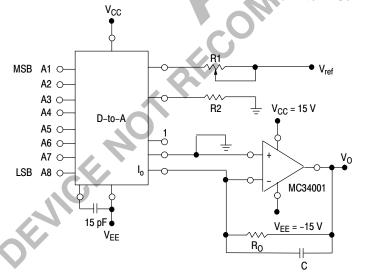


Figure 12. Output Current to Voltage Transformation for a D-to-A Converter



Settling time to within 1/2 LSB is approximately 4.0  $\mu s$  from the time all bits are switched (C = 68 pF).

The value of C may be selected to minimize overshoot and ringing.

Theoretical V<sub>O</sub>

$$V_{O} = \ \frac{V_{ref}}{R1} \ (R_{O}) \ \Big[ \ \frac{A1}{2} \ + \frac{A2}{4} \ + \ \frac{A3}{8} \ + \frac{A4}{16} \ + \ \frac{A5}{32} \ + \ \frac{A6}{64} \ + \ \frac{A7}{128} \ + \frac{A8}{256} \ \Big]$$

Figure 13. Positive Peak Detector

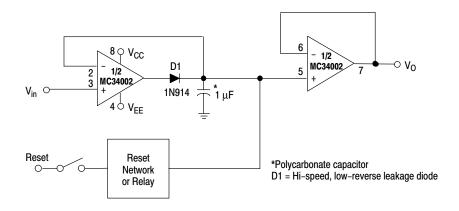
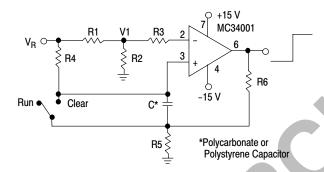


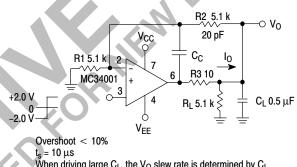
Figure 14. Long Interval RC Timer



Time (t) = R4 Cn  $(V_R/V_R-V_I)$ ,  $R_3 = R_4$ ,  $R_5 = 0.1 R_6$ If R1 = R2: t = 0.693 R4C

Design Example: 100 Second Timer  $V_R = 10 \text{ V}$   $C = 1.0 \,\mu\text{F}$   $R3 = R4 = 144 \,\text{M}$ R6 = 20 k R5 = 2.0 k R1 = R2 = 1.0 k

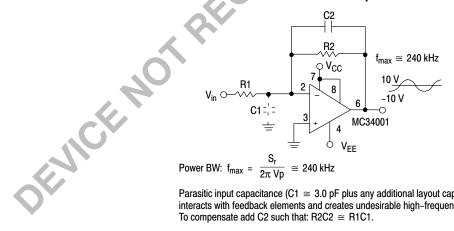
Figure 15. Isolating Large Capacitive Loads



 $t_s$  = 10  $\mu s$  When driving large  $C_L$  , the  $V_O$  slew rate is determined by  $C_L$ and I<sub>O(max)</sub>:

$$\frac{\Delta V_0}{\Delta t} = \frac{I_0}{C_L} = \frac{0.02}{0.5} \quad \text{V/}\mu\text{s} = 0.04 \text{ V/}\mu\text{s} \text{ (with } C_L \text{ shown)}$$

Figure 16. Wide BW, Low Noise, **Low Drift Amplifier** 

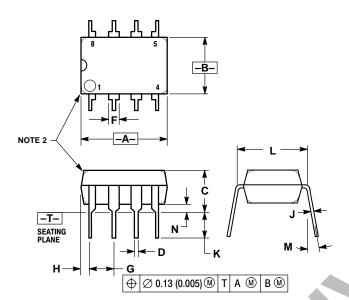


Parasitic input capacitance (C1 ≅ 3.0 pF plus any additional layout capacitance) interacts with feedback elements and creates undesirable high-frequency pole. To compensate add C2 such that:  $R2C2 \cong R1C1$ .

### **OUTLINE DIMENSIONS**

### **P SUFFIX**

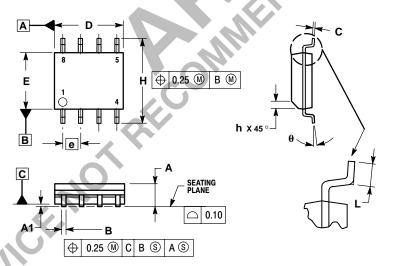
PLASTIC PACKAGE CASE 626-05 ISSUE K



- NOTES:
  1. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
  2. PACKAGE CONTOUR OPTIONAL (ROUND OR SQUARE CORNERS).
  3. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	9.40	10.16	0.370	0.400
В	6.10	6.60	0.240	0.260
С	3.94	4.45	0.155	0.175
D	0.38	0.51	0.015	0.020
F	1.02	1.78	0.040	0.070
G	2.54 BSC		0.100 BSC	
Н	0.76	1.27	0.030	0.050
J	0.20	0.30	0.008	0.012
K	2.92	3.43	0.115	0.135
L	7.62	BSC	0.300	BSC
M		10°	4	10°
N	0.76	1.01	0.030	0.040





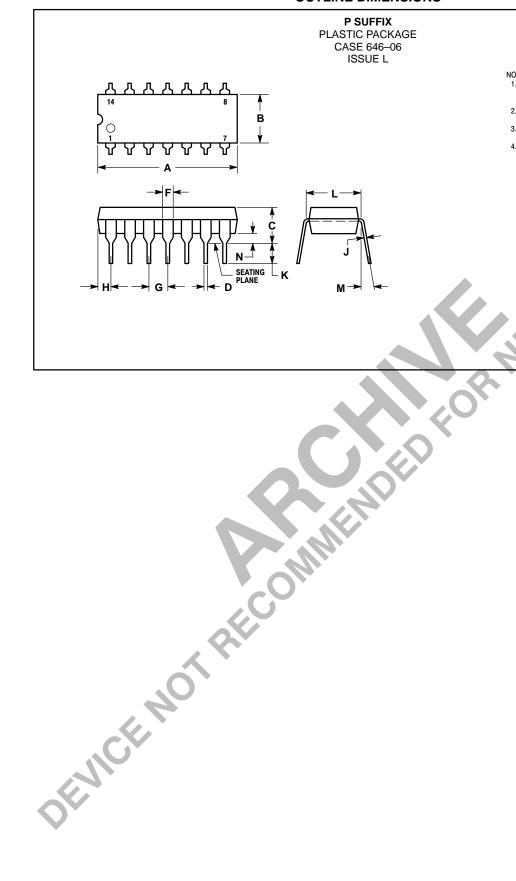
### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. DIMENSIONS ARE IN MILLIMETERS.
  3. DIMENSION D AND E DO NOT INCLUDE MOLD
- MINENSION D AND E DO NOT INCLUDE MOLD PROTRUSION.
   MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
   DIMENSION B DOES NOT INCLUDE MOLD PROTRUSION. ALLOWABLE DAMBAR

PROTRUSION SHALL BE 0.127 TOTAL IN EXCESS OF THE B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		
DIM	MIN	MAX	
Α	1.35	1.75	
A1	0.10	0.25	
В	0.35	0.49	
С	0.18	0.25	
D	4.80	5.00	
Е	3.80	4.00	
е	1.27	BSC	
Н	5.80	6.20	
h	0.25	0.50	
L	0.40	1.25	
θ	0 °	7 °	

### **OUTLINE DIMENSIONS**



#### NOTES:

- LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE
   POSITION AT SEATING PLANE AT MAXIMUM
   MATERIAL CONDITION.
- DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
- DIMENSION B DOES NOT INCLUDE MOLD FLASH.
- 4. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	19.56
В	0.240	0.260	6.10	6.60
С	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
Н	0.052	0.095	1.32	2.41
L	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
٦	0.300	0.300 BSC		BSC
M	0°	10°	0°	10°
N	0.015	0.039	0.39	1.01







ON Semiconductor is a trademark and is a registered trademark of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

### **PUBLICATION ORDERING INFORMATION**

### Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

**Phone:** 303–675–2175 or 800–344–3860 Toll Free USA/Canada **Fax:** 303–675–2176 or 800–344–3867 Toll Free USA/Canada

Email: ONlit@hibbertco.com

N. American Technical Support: 800–282–9855 Toll Free USA/Canada

**JAPAN**: ON Semiconductor, Japan Customer Focus Center 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–0031

**Phone**: 81–3–5740–2700 **Email**: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local

Sales Representative.